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(54) Title: NANOSHEET SIZING FOR POWER DELIVERY

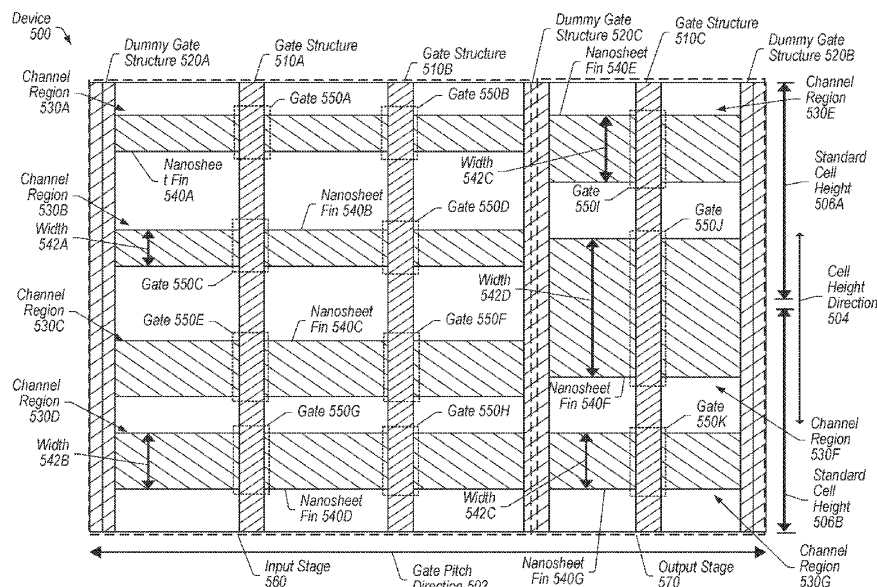


FIG. 5

(57) Abstract: Various structures that implement nanosheet transistors are disclosed. The various structures include nanosheet transistors with different widths inside a transistor device. Variation of the width of nanosheet transistors within a transistor device allows for different designs of the input stage and the output stage of the transistor device that may improve power utilization and performance of the transistor device. In some instances, the input stage has nanosheet transistors with smaller width nanosheet fins than nanosheet transistors in the output stage. Variations in nanosheet transistor width may also be implemented within the input stage or the output stage by merging of nanosheet fins.

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